



JT075N065WED

主要参数 MAIN CHARACTERISTICS

Ic	75A
Vces	650V
Vcesat-typ	1.7V

用途

- 逆变器
- UPS 电源

APPLICATIONS

- General purpose inverters
- UPS

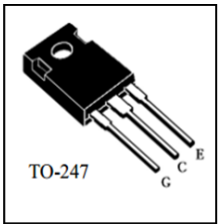
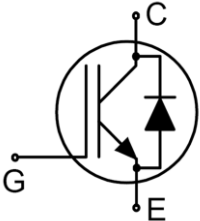
产品特性

- 低栅极电荷
- Trench FS 技术,
- RoHS 产品

FEATURES

- Low gate charge
- Trench FS Technology,
- RoHS product

封装 Package



订货信息 ORDER MESSAGE

订 货 型 号 Order codes				印 记 Marking	封 装 Package
有卤-条管 Halogen-Tube	无卤-条管 Halogen-Free-Tube	有卤-编带 Halogen-Reel	无卤-编带 Halogen-Free-Reel		
JT075N065WED-GE-B	JT075N065WED-GE-BR	N/A	N/A	JT075N065WED	TO-247



绝对最大额定值 ABSOLUTE RATINGS ($T_C=25^{\circ}\text{C}$)

项 目 Parameter	符 号 Symbol	数 值 Value	单 位 Unit
最高集电极—发射极直流电压 Collector-Emmitter Voltage	V_{CES}	650	V
*连续集电极电流 Collector Current-continuous	I_C	150($T_C=25^{\circ}\text{C}$)	A
		75($T_C=100^{\circ}\text{C}$)	A
最大脉冲集电极极电流 (注 1) Collector Current – pulse (note 1)	I_{CM}	300	A
二极管正向测试电流 Diode RMS forward current	I_F	150($T_C=25^{\circ}\text{C}$)	A
		75 ($T_C=100^{\circ}\text{C}$)	A
二极管正向不重复峰值电流 (浪涌电流) Surge non repetitive forward current $t_p=10\text{ ms}$ sinusoidal	I_{FSM}	300	A
最高栅极发射极电压 Gate-Emmitter Voltage	V_{GES}	± 20	V
瞬态栅极发射极电压 Transient Gate-emitter voltage($t_p \leq 10\mu\text{s}$, $D < 0.010$)	V_{GES}	± 30	V
安全工作区 Turn-off safe area	-	300	A
耗散功率 Power Dissipation	P_D $T_C=25^{\circ}\text{C}$	539	W
最高结温及存储温度 Operating and Storage Temperature Range	T_J , T_{STG}	$-55 \sim +150$	$^{\circ}\text{C}$
引线最高焊接温度 Maximum Lead Temperature for Soldering Purposes	T_L	300	$^{\circ}\text{C}$

*连续集电极电流由最高结温限制

*Collector current limited by maximum junction temperature

注释:

1: 脉冲宽度由最高结温限制

Notes:

1: Pulse width limited by maximum junction temperature





电特性 ELECTRICAL CHARACTERISTICS

项 目 Parameter	符 号 Symbol	测试条件 Tests conditions	最小 Min	典型 Typ	最大 Max	单位 Units
关态特性 Off –Characteristics						
集电极—发射极击穿电压 Collector-Emmitter Voltage	BV_{CES}	$I_C=250\mu A, V_{GE}=0V$	650	-	-	V
零栅压下集电极漏电流 Zero Gate Voltage Collector Current	I_{CES}	$V_{CE}=650V, V_{GE}=0V, T_C=25^\circ C$	-	-	0.2	mA
正向栅极体漏电流 Gate-body leakage current, forward	I_{GESF}	$V_{CE}=0V, V_{GE}=20V$	-	-	200	nA
反向栅极体漏电流 Gate-body leakage current, reverse	I_{GESR}	$V_{CE}=0V, V_{GE}=-20V$	-	-	-200	nA
通态特性 On-Characteristics						
阈值电压 Gate Threshold Voltage	$V_{GE(th)}$	$V_{CE} = V_{GE}, I_C=250\mu A$	4.5	-	6.5	V
饱和压降 Collector-Emmitter saturation Voltage	V_{CESAT}	$V_{GE}=15V, I_C=75A, T_C=25^\circ C$	-	1.7	2.4	V
动态特性 Dynamic Characteristics						
输入电容 Input capacitance	C_{ies}	$V_{CE}=25V, V_{GE}=0V, f=1.0MHz$	-	5012	-	pF
输出电容 Output capacitance	C_{oes}		-	430	-	pF
反向传输电容 Reverse transfer capacitance	C_{res}		-	99.6	-	pF
栅极电荷总量 Total Gate Charge	Q_g	$V_{CC}=520V, I_C=75A, R_G=7.9\Omega, V_{GE}=15V, T_C=25^\circ C$	-	170	-	nC
栅极-反射极 Gate to emitter charge	Q_{ge}		-	43	-	
栅极-集电极 Gate to collector charge	Q_{gc}		-	78	-	
栅极电阻-Gate resistance	R_g	$f=1\text{ MHz, open collector}$	-	3	-	Ω
短路电流-short current	I_{sc}	$V_{GE}=15V, V_{CE}=300V, t_{sc} \leq 10\mu s$	-	300	-	A





电特性 ELECTRICAL CHARACTERISTICS

开关特性 Switching Characteristics

项 目 Parameter	符 号 Symbol	测试条件 Tests conditions	最小 Min	典型 Typ	最大 Max	单位 Units
开启延迟时间 Turn-On delay time	$t_{d(on)}$	$V_{CC}=400V, I_c=75A, R_G=7.9\Omega$ $V_{GE}=15V$ $T_C=25^\circ C$	-	87	-	ns
上升时间 Turn-On rise time	t_r		-	156	-	ns
关断延迟时间 Turn-Off delay time	$t_{d(off)}$		-	168	-	ns
下降时间 Turn-Off Fall time	t_f		-	86	-	ns
开通损耗 Turn-On energy	Eon		-	3.4	-	mJ
关断损耗 Turn-off energy	Eoff		-	1.8	-	mJ
总开关损耗 Total switching energy	Etot		-	5.2	-	mJ
开启延迟时间 Turn-On delay time	$t_{d(on)}$	$V_{CC}=400V, I_c=75A, R_G=7.9\Omega$ $V_{GE}=15V$ $T_C=150^\circ C$	-	85	-	ns
上升时间 Turn-On rise time	t_r		-	154	-	ns
关断延迟时间 Turn-Off delay time	$t_{d(off)}$		-	190	-	ns
下降时间 Turn-Off Fall time	t_f		-	99	-	ns
开通损耗 Turn-On energy	Eon		-	4.2	-	mJ
关断损耗 Turn-off energy	Eoff		-	2.2	-	mJ
总开关损耗 Total switching energy	Etot		-	6.4	-	mJ

反并联二极管特性及最大额定值 Anti-Parallel Diode Characteristics and Maximum Ratings

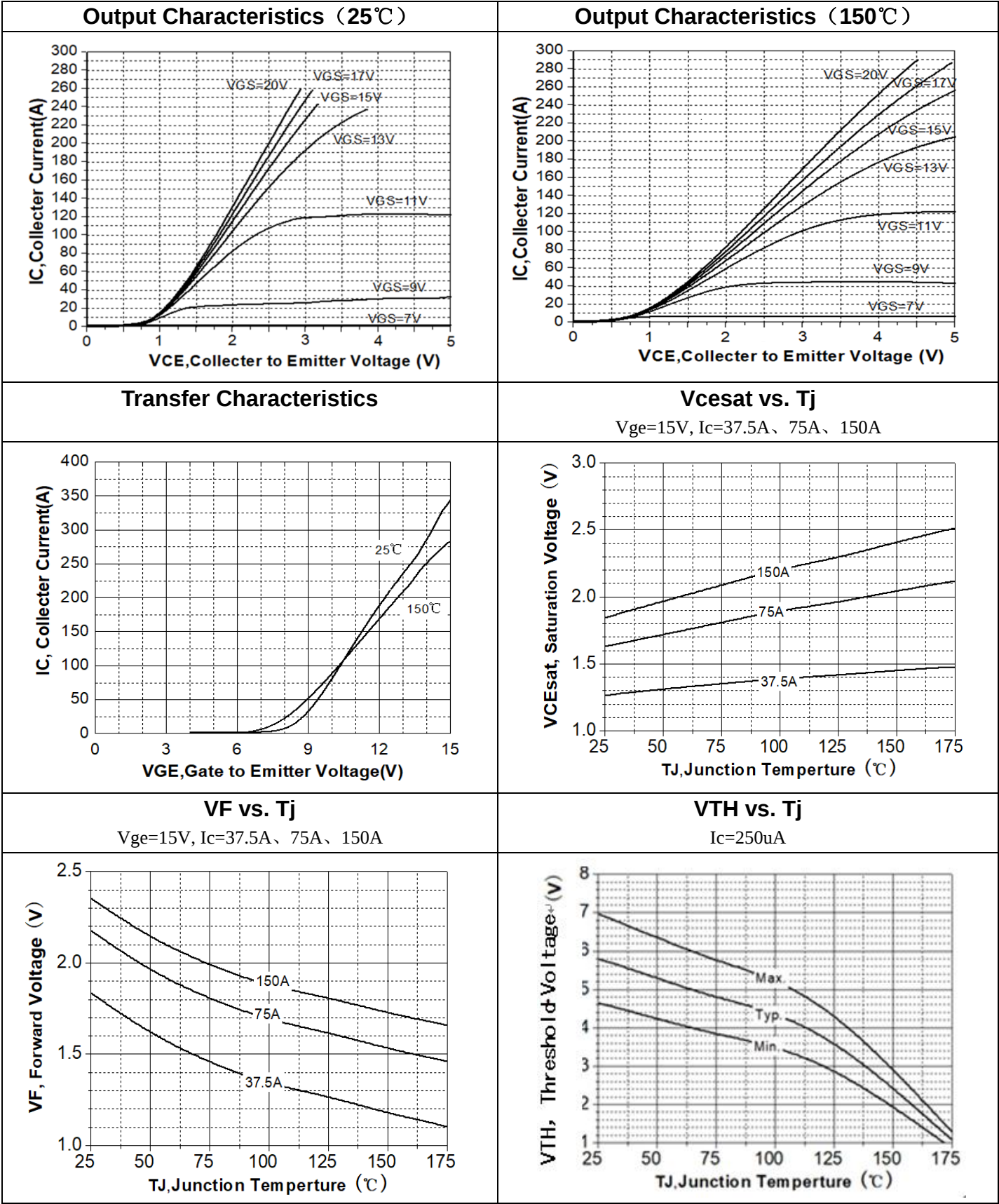
正向压降 Drain-Source Diode Forward Voltage	V_F	$V_{GE}=0V, I_S=75A$	-	2.2	2.9	V
反向恢复时间 Diode Reverse recovery time	t_{rr}	$V_{GE}=0V, V_R=200V, I_F=75A$ $dI_F/dt=200A/\mu s$ $T_C=25^\circ C$	-	24.5	-	ns
反向恢复电荷 Diode Reverse recovery charge	Qrr		-	20.6	-	nC
反向恢复电流 Diode Reverse recovery Current	I_{RRM}		-	1.64	-	A
反向恢复时间 Diode Reverse recovery time	t_{rr}	$V_{GE}=0V, V_R=200V, I_F=75A$ $dI_F/dt=200A/\mu s$ $T_C=150^\circ C$	-	195	-	ns
反向恢复电荷 Diode Reverse recovery charge	Qrr		-	731	-	nC
反向恢复电流 Diode Reverse recovery Current	I_{RRM}		-	8.3	-	A

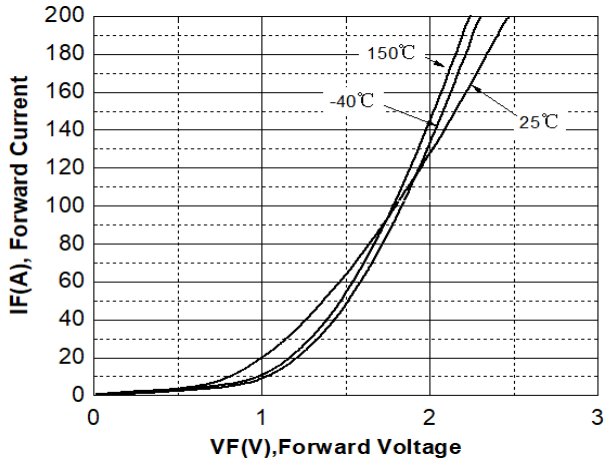
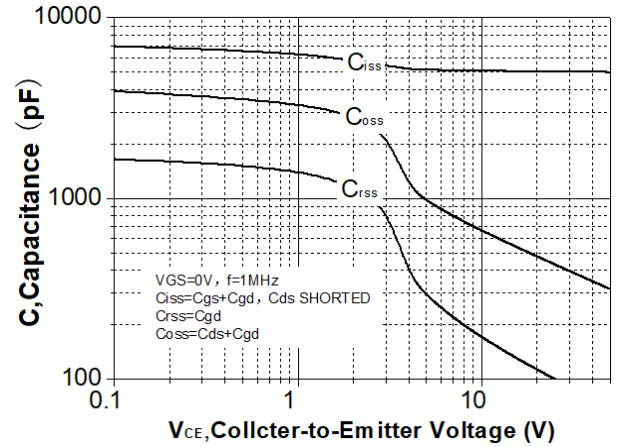
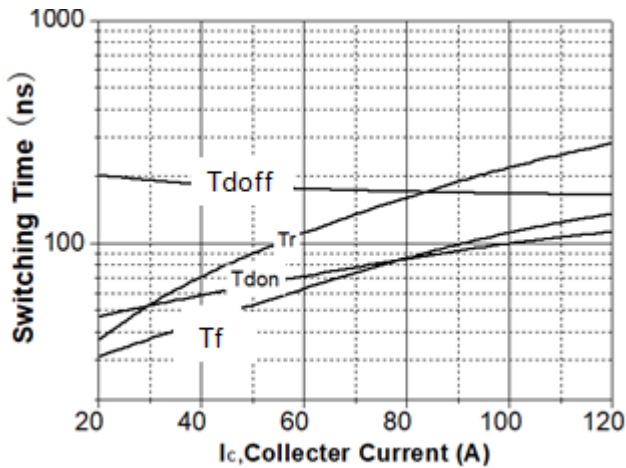
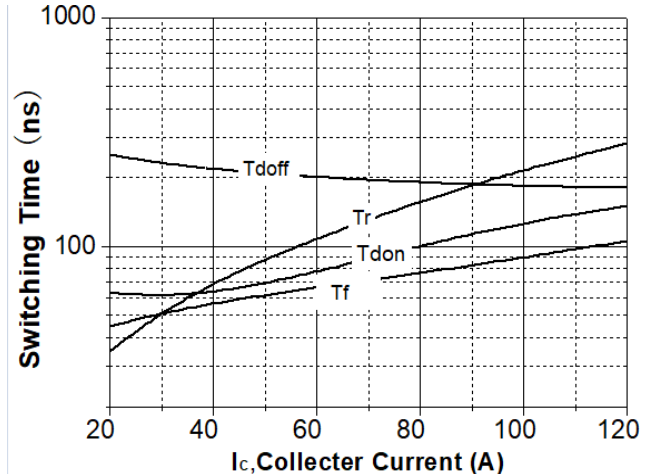
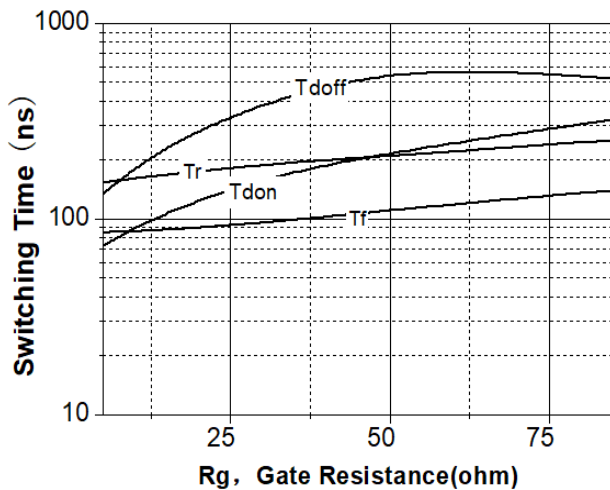
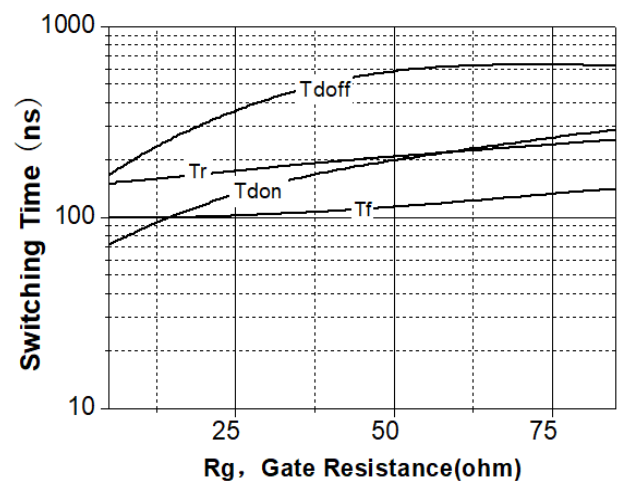
项 目 Parameter	符 号 Symbol	MAX	单 位 Unit
结到管壳的热阻 Junction to Case IGBT	$R_{th(j-c)}$	0.232	$^\circ C/W$
结到管壳的热阻 Junction to Case diode	$R_{th(j-c)}$	0.38	$^\circ C/W$
结到环境的热阻 Junction to Ambient	$R_{th(j-A)}$	40	$^\circ C/W$

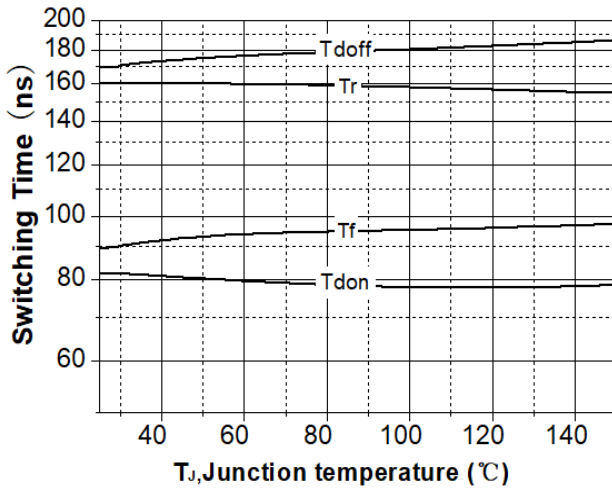
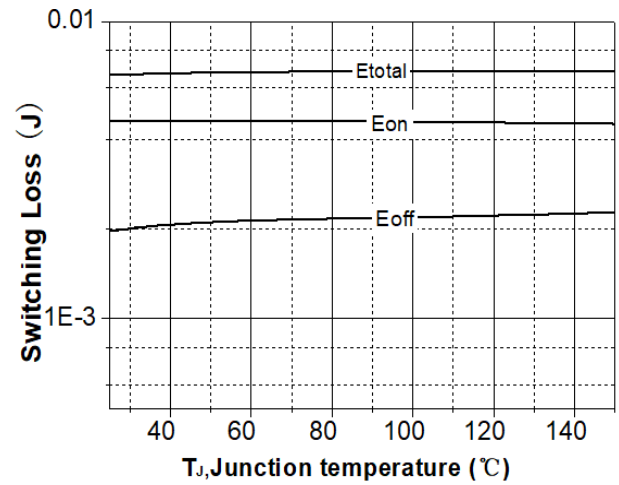
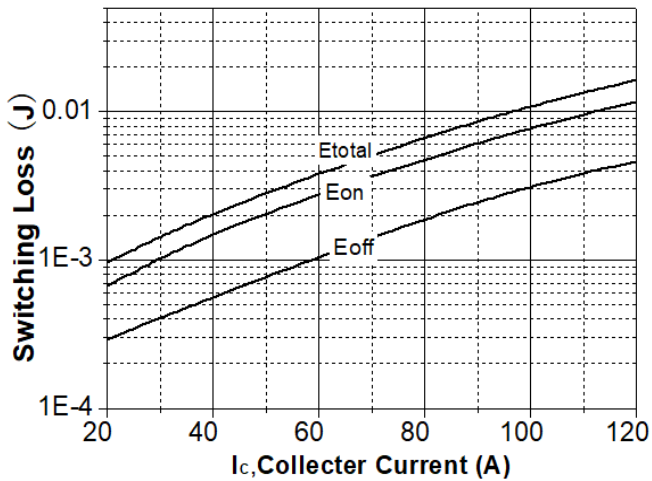
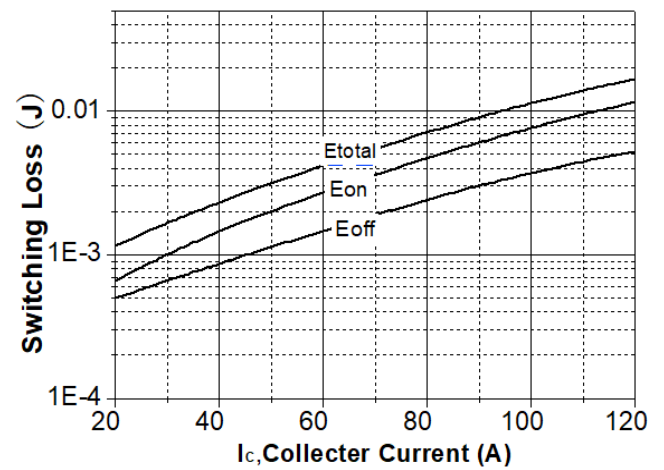
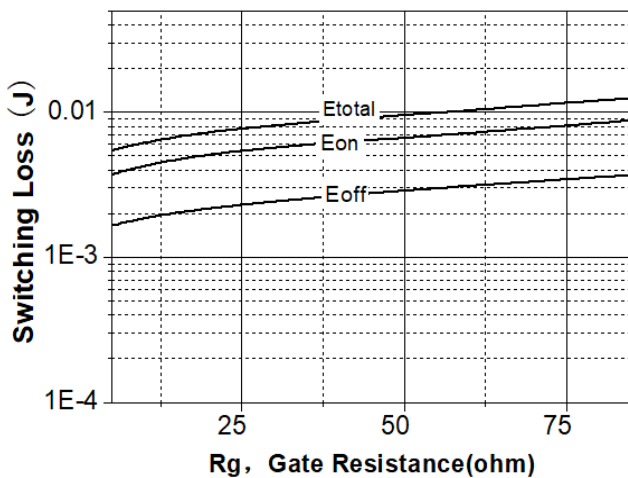
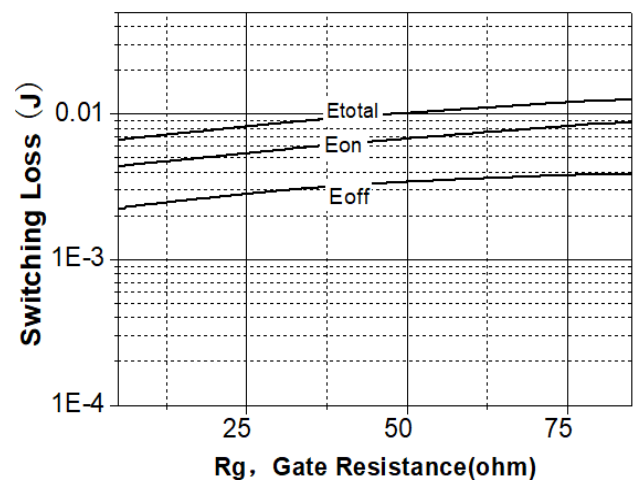


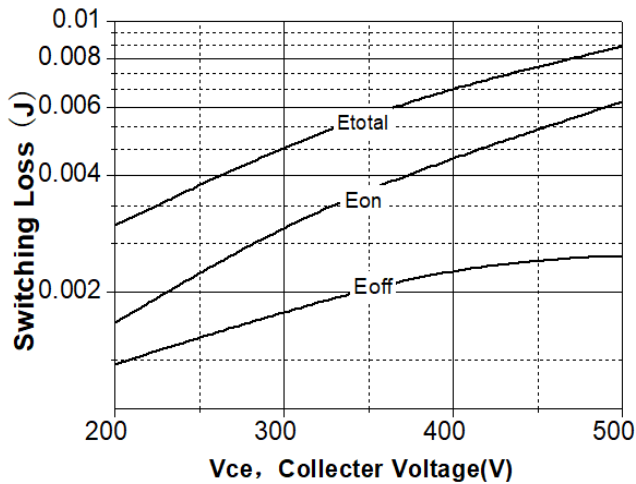
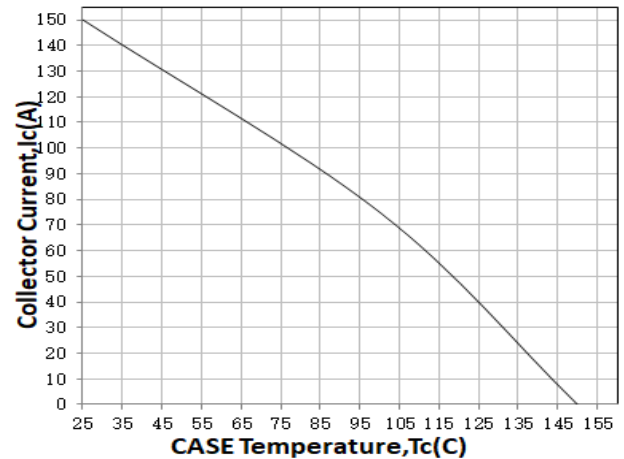
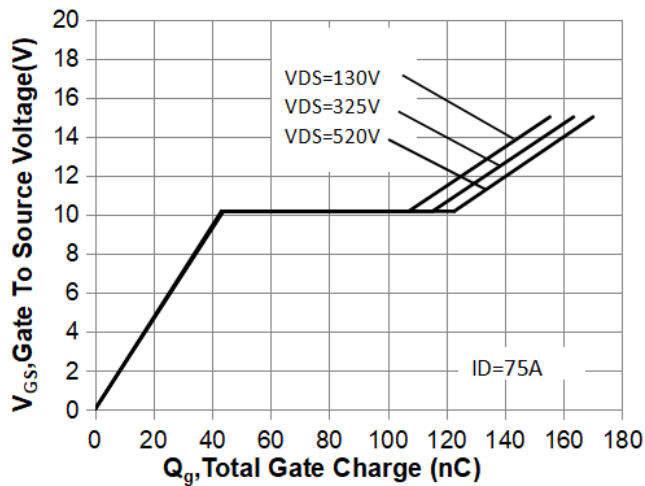
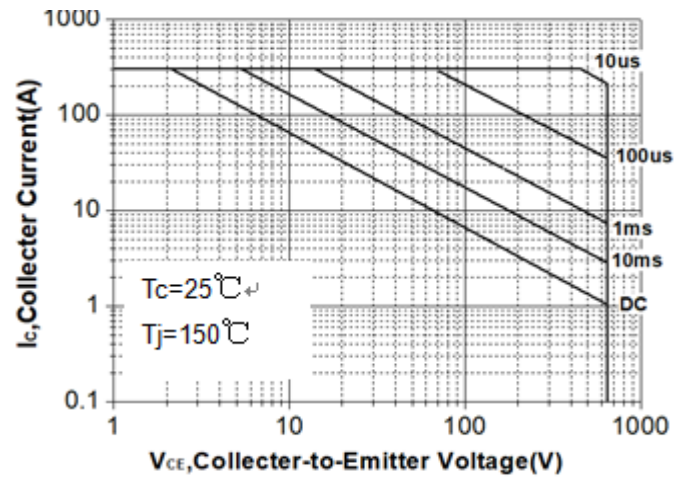
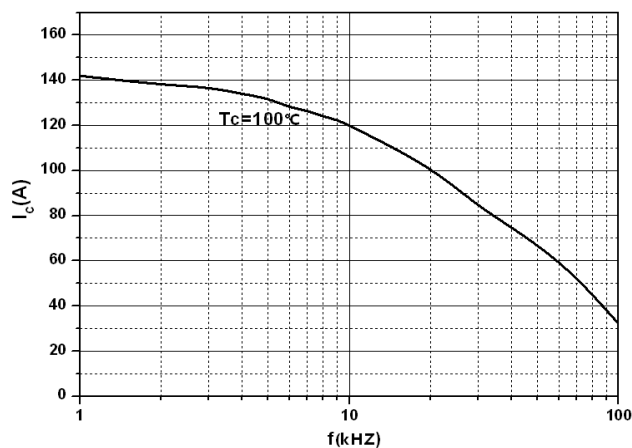
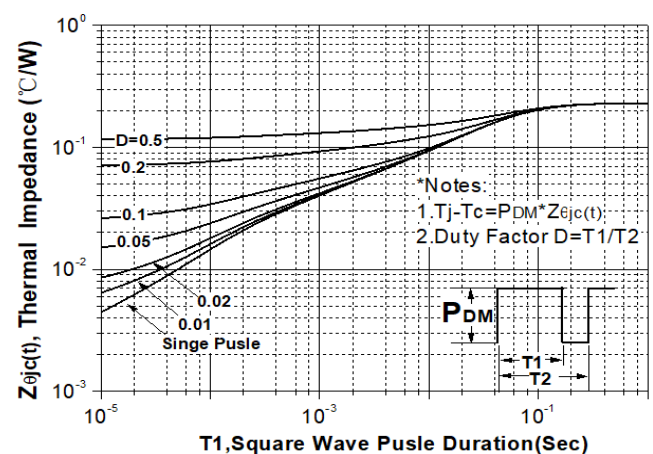


特征曲线 ELECTRICAL CHARACTERISTICS (curves)



**Diode Characteristic** $T_j = 25^\circ\text{C}, 150^\circ\text{C}, -40^\circ\text{C}$ **Capacitance Characteristic** $V_{ge} = 0\text{V}, f = 1.0\text{MHz}$ **Switching Time vs. IC(25°C)** $V_{ce} = 400\text{V}, V_{ge} = 15\text{V}, R_g = 7.9\Omega$ **Switching Time vs. IC(150°C)** $V_{ce} = 400\text{V}, V_{ge} = 15\text{V}, R_g = 7.9\Omega$ **Switching Time vs. Rg(25°C)** $V_{ge} = 15\text{V}, V_{ce} = 400\text{V}, I_c = 75\text{A}$ **Switching Time vs. Rg(150°C)** $V_{ge} = 15\text{V}, V_{ce} = 400\text{V}, I_c = 75\text{A}$ 

**Switching Time vs. T_j** $V_{ge}=15V, V_{ce}=400V, I_c=75A, R_g=7.9\Omega$ **Switching Loss vs. T_j** $V_{ge}=15V, V_{ce}=400V, I_c=75A, R_g=7.9\Omega$ **Switching Loss vs. $I_c(25^\circ C)$** $V_{ge}=15V, V_{ce}=400V, R_g=7.9\Omega$ **Switching Loss vs. $I_c(150^\circ C)$** $V_{ge}=15V, V_{ce}=400V, R_g=7.9\Omega$ **Switching Loss vs. $R_g(25^\circ C)$** $V_{ge}=15V, V_{ce}=400V, I_c=75A$ **Switching Loss vs. $R_g(150^\circ C)$** $V_{ge}=15V, V_{ce}=400V, I_c=75A$ 

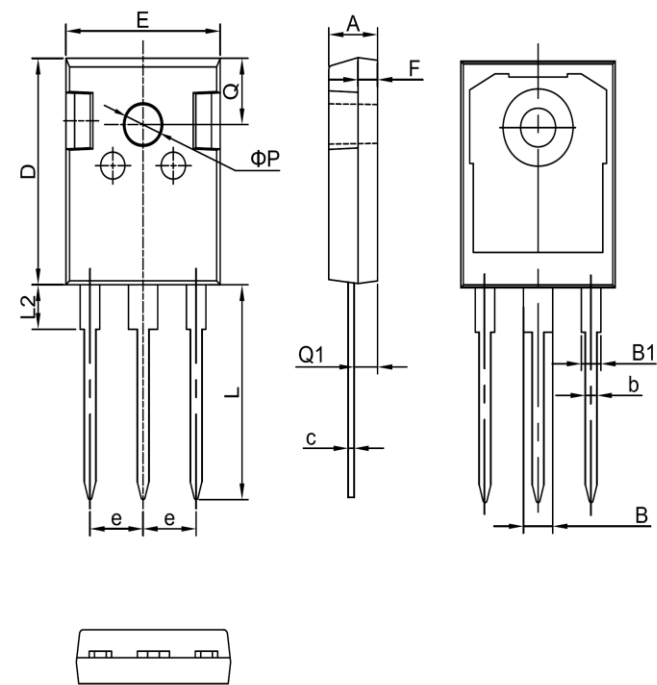
**Switching Loss vs. VCE(150℃)** $V_{ge}=15V, I_c=75A, R_g=7.9\Omega$ **Collector current vs.case temperature** $V_{ge}\geq 15V, T_j\leq 150^\circ C$ **Gate Charge Characteristics** $V_{ge}=15V, I_c=75A$ **Safe Operating Area For TO-247** $T_c=25^\circ C, V_{ge}=15V, T_j\leq 150^\circ C$ **Ic vs. f** $V_{cc}=400V, R_g=4.7\Omega, V_{ge}=15V, \text{duty cycle}=0.5$ **Transient Thermal Impedance for IGBT**



外形尺寸 PACKAGE MECHANICAL DATA

TO-247

单位 Unit: mm



符号 symbol	MIN	MAX
A	4.90	5.10
B	2.95	3.35
B1	1.95	2.35
b	1.15	1.35
c	0.50	0.70
D	20.90	21.10
E	15.70	15.90
e	5.34	5.54
F	1.90	2.10
L	19.40	20.40
L2	4.03	4.23
Q	6.00	6.40
Q1	2.30	2.50
P	3.50	3.70



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